

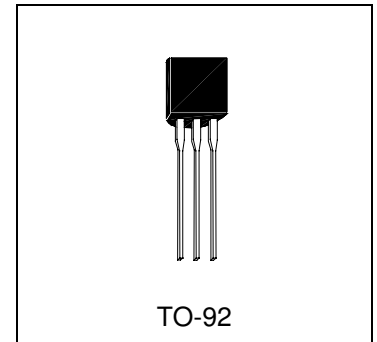


H2N7000

N-Channel Enhancement Mode Transistor

Description

The H2N7000 is designed for high voltage, high speed applications such as switching regulators, converters, solenoid and relay drivers.



Absolute Maximum Ratings

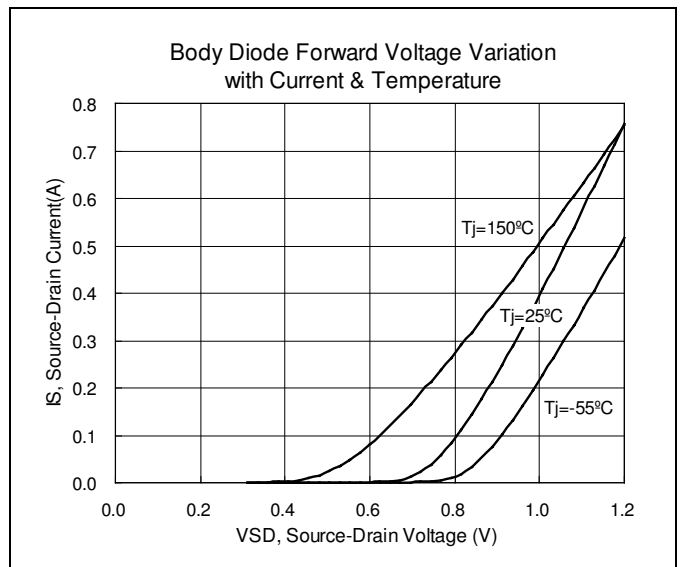
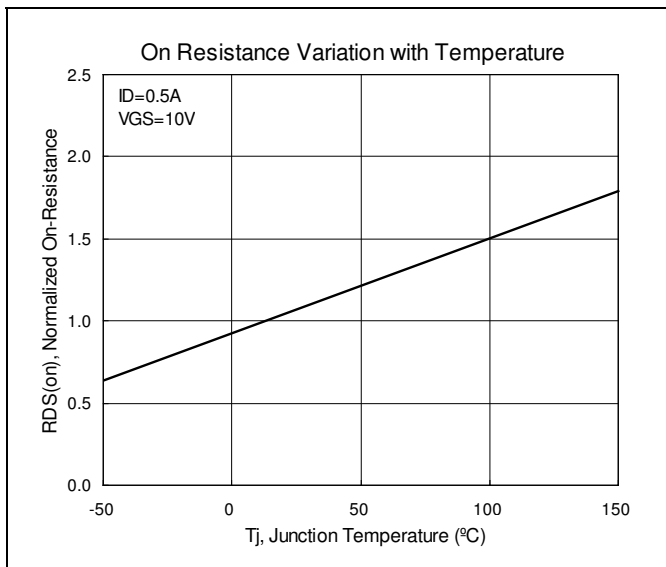
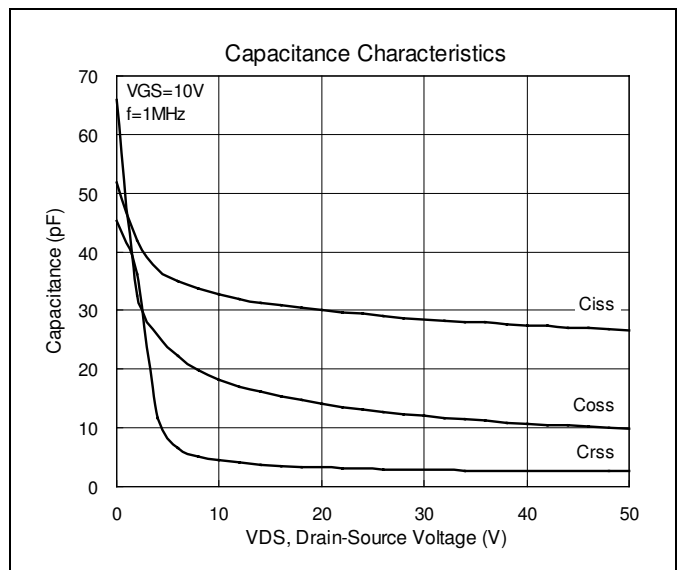
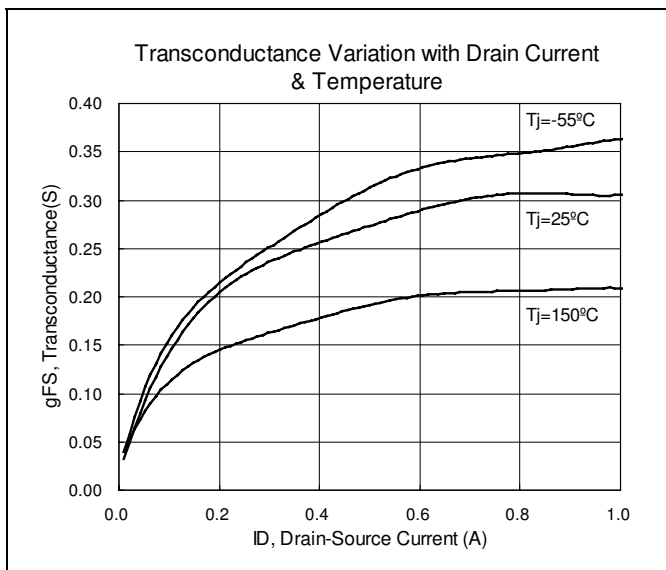
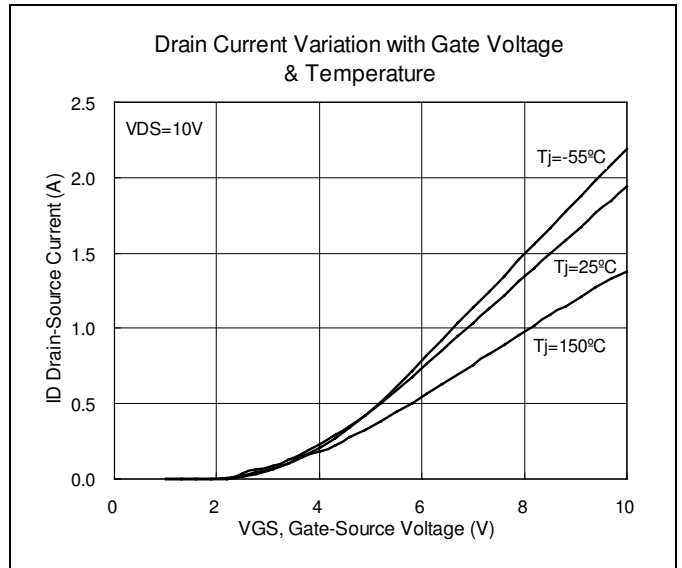
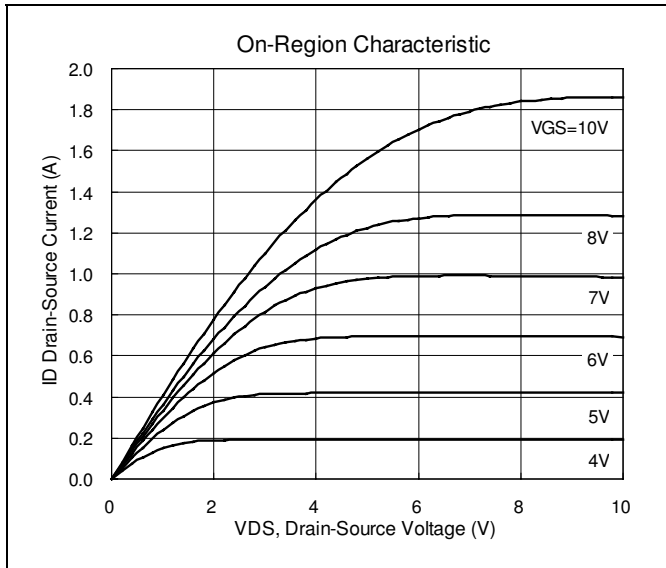
- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (T_A=25°C) 400 mW
- Maximum Voltages and Currents (T_A=25°C)
 - BV_{DSS} Drain to Source Voltage 60 V
 - BV_{GSS} Gate to Source Voltage 40 V
 - I_D Drain Current 200 mA

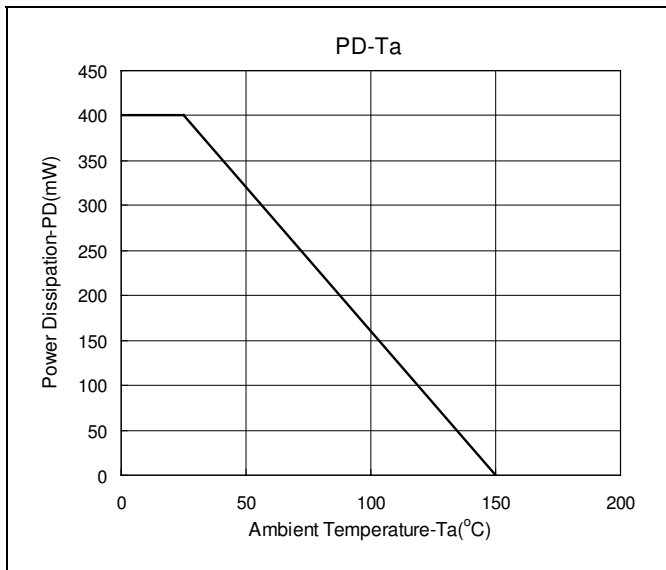
Electrical Characteristics (T_A=25°C)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
Drain-Source Voltage	V _{DSS}	I _D =10uA, V _{GS} =0	60	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V	-	1	uA
Gate Source Leakage Current	I _{GSS}	V _{GS} =±15V	-	±10	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =3V, I _D =1mA	0.8	3	V
On-State Drain Current	I _{D(on)}	V _{GS} =4.5V, V _{DS} =10V	75	-	mA
Static Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =0.5A	-	5	Ω
Static Drain-Source On-State Voltage	V _{DS(on)1}	V _{GS} =10V, I _D =0.5A	-	2.5	V
	V _{DS(on)2}	V _{GS} =4.5V, I _D =75mA	-	0.4	v



Characteristics Curve







TO-92 Dimension

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

H	2	N
7	0	0

Date Code Control Code

Note: Green label is used for pb-free packing
 Pin Style: Pin 1.Source 2.Gate 3.Drain

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

*: Typical, Unit: mm

3-Lead TO-92 Plastic Package
 HSMC Package Code: A

TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1,F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

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Head Office And Factory:

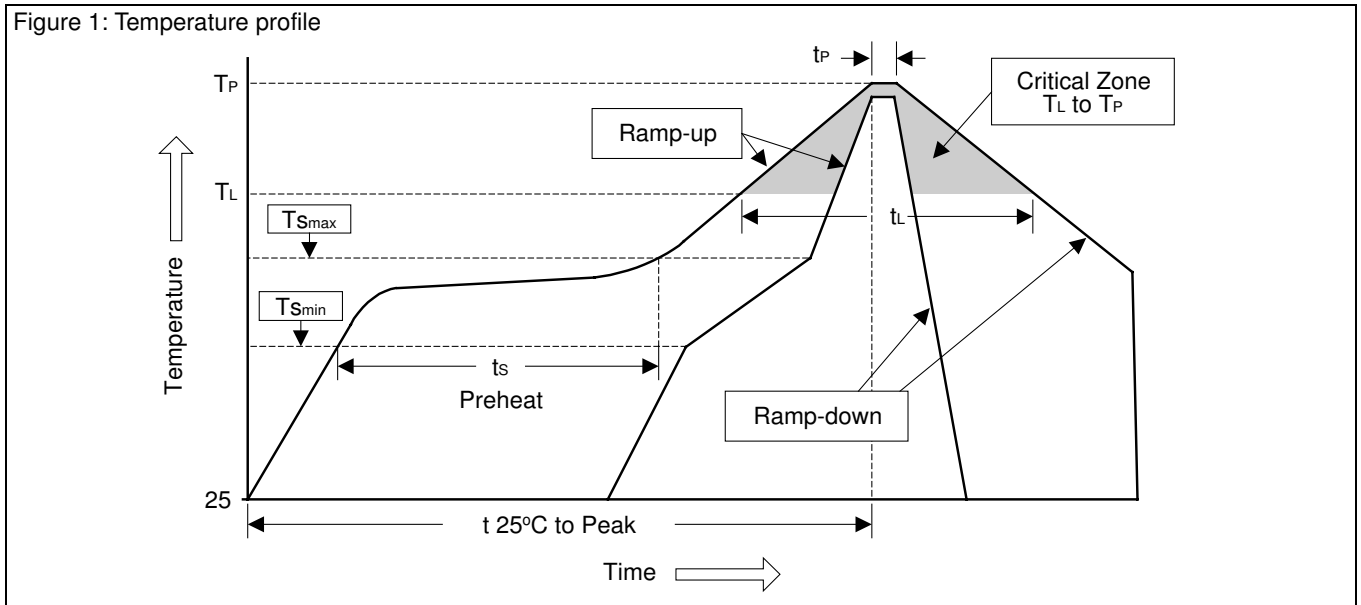
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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec